AMD Xilinx - XC7K325T-1FFG900CES Datasheet

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Details	
Product Status	Obsolete
Number of LABs/CLBs	25475
Number of Logic Elements/Cells	326080
Total RAM Bits	16404480
Number of I/O	500
Number of Gates	-
Voltage - Supply	0.97V ~ 1.03V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	900-BBGA, FCBGA
Supplier Device Package	900-FCBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7k325t-1ffg900ces

Table 1: **Absolute Maximum Ratings (1) *(Cont'd)***

Symbol	Description	Min	Max	Units
I_{DCIN}	DC input current for receiver input pins DC coupled $V_{MGTAVTT}$ = 1.2V	–	14	mA
I_{DCOUT}	DC output current for transmitter pins DC coupled $V_{MGTAVTT}$ = 1.2V	–	14	mA
XADC				
V_{CCADC}	XADC supply relative to GNDADC	–0.5	2.0	V
V_{REFP}	XADC reference input relative to GNDADC	–0.5	2.0	V
Temperature				
T_{STG}	Storage temperature (ambient)	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies (6)	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies (6)	–	+260	°C
T_j	Maximum junction temperature(6)	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. The lower absolute voltage specification always applies.
3. For I/O operation, refer to UG471: *7 Series FPGAs SelectIO Resources User Guide*.
4. The maximum limit applied to DC and AC signals.
5. For maximum undershoot and overshoot AC specifications, see Table 4 and Table 5.
6. For soldering guidelines and thermal considerations, see UG475: *7 Series FPGA Packaging and Pinout Specification*.

Table 2: **Recommended Operating Conditions (1)**

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V_{CCINT}(2)	Internal supply voltage	0.97	1.00	1.03	V
	For -2L (0.9V) devices: internal supply voltage	0.87	0.90	0.93	V
V_{CCBRAM}(2)	Block RAM supply voltage	0.97	1.00	1.03	V
	For -2L (0.9V) devices: block RAM supply voltage	0.87	0.90	1.03	V
V_{CCAUX}	Auxiliary supply voltage	1.71	1.80	1.89	V
V_{CCO}(3)(4)	Supply voltage for 3.3V HR I/O banks	1.14	–	3.465	V
	Supply voltage for 1.8V HP I/O banks	1.14	–	1.89	V
V_{CCAUX_IO}	Auxiliary supply voltage when set to 1.8V	1.71	1.80	1.89	V
	Auxiliary supply voltage when set to 2.0V	1.94	2.00	2.06	V
V_{IN}(5)	I/O input voltage	–0.20	–	V_{CCO} + 0.2	V
	I/O input voltage for V_{REF} and differential I/O standards	–0.20	–	2.625	V
I_{IN}(6)	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
V_{CCBATT}(7)	Battery voltage	1.0	–	1.89	V
GTX Transceiver					
$V_{MGTAVCC}$(8)	Analog supply voltage for the GTX transceiver QPLL frequency range ≤ 10.3125 GHz(9)(10)	0.97	1.0	1.08	V
	Analog supply voltage for the GTX transceiver QPLL frequency range > 10.3125 GHz	1.02	1.05	1.08	V
$V_{MGTAVTT}$(8)	Analog supply voltage for the GTX transmitter and receiver termination circuits	1.17	1.2	1.23	V
$V_{MGTVCCAUX}$(8)	Auxiliary analog QPLL voltage supply for the transceivers	1.75	1.80	1.85	V

Table 2: **Recommended Operating Conditions (1) *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
$V_{MGTAVTTRCAL}$ (8)	Analog supply voltage for the resistor calibration circuit of the GTX transceiver column	1.17	1.2	1.23	V
XADC					
V_{CCADC}	XADC supply relative to GNDADC	1.71	1.80	1.89	V
V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	–	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	–	100	°C

Notes:

1. All voltages are relative to ground.
2. V_{CCINT} and V_{CCBRAM} should be connected to the same supply.
3. Configuration data is retained even if V_{CCO} drops to 0V.
4. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
5. The lower absolute voltage specification always applies.
6. A total of 200 mA per bank should not be exceeded.
7. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX}.
8. Each voltage listed requires the filter circuit described in UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide*.
9. For data rates ≤ 10.3125 Gb/s, $V_{MGTAVCC}$ should be 1.0V ±3% for lower power consumption.
10. For lower power consumption, $V_{MGTAVCC}$ should be 1.0V ±3% over the entire CPLL frequency range.

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	15	µA
C_{IN} (2)	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V	90	–	330	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	68	–	250	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	34	–	220	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	23	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.3V	68	–	330	µA
	Pad pull-down (when selected) @ V_{IN} = 1.8V	45	–	180	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state	–	–	25	mA
I_{BATT} (3)	Battery supply current	–	–	150	nA

Table 3: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ[1]	Max	Units
R_{IN_TERM}[4]	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_40) for commercial (C), industrial (I), and extended (E) temperature devices	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_50) for commercial (C), industrial (I), and extended (E) temperature devices	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_60) for commercial (C), industrial (I), and extended (E) temperature devices	44	60	83	Ω
n	Temperature diode ideality factor	–	1.010	–	–
r	Temperature diode series resistance	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a $V_{CCO}/2$ level.

Table 4: **Maximum Allowed AC Voltage Overshoot and Undershoot for 3.3V HR I/O Banks[1]**

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
V_{CCO} + 0.40	100	–0.40	100
V_{CCO} + 0.45	100	–0.45	61.7
V_{CCO} + 0.50	100	–0.50	25.8
V_{CCO} + 0.55	100	–0.55	11.0
V_{CCO} + 0.60	46.6	–0.60	4.77
V_{CCO} + 0.65	21.2	–0.65	2.10
V_{CCO} + 0.70	9.75	–0.70	0.94
V_{CCO} + 0.75	4.55	–0.75	0.43
V_{CCO} + 0.80	2.15	–0.80	0.20
V_{CCO} + 0.85	1.02	–0.85	0.09
V_{CCO} + 0.90	0.49	–0.90	0.04
V_{CCO} + 0.95	0.24	–0.95	0.02

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 5: **Maximum Allowed AC Voltage Overshoot and Undershoot for 1.8V HP I/O Banks[1][2]**

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
V_{CCO} + 0.40	100	–0.40	100
V_{CCO} + 0.45	100	–0.45	100
V_{CCO} + 0.50	100	–0.50	100
V_{CCO} + 0.55	100	–0.55	100
V_{CCO} + 0.60	50.0	–0.60	50.0
V_{CCO} + 0.65	50.0	–0.65	50.0
V_{CCO} + 0.70	47.0	–0.70	50.0
V_{CCO} + 0.75	21.2	–0.75	50.0

Table 5: **Maximum Allowed AC Voltage Overshoot and Undershoot for 1.8V HP I/O Banks(1)(2) *(Cont'd)***

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
V_{CCO} + 0.80	9.71	–0.80	50.0
V_{CCO} + 0.85	4.51	–0.85	28.4
V_{CCO} + 0.90	2.12	–0.90	12.7
V_{CCO} + 0.95	1.01	–0.95	5.79

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 µs.

Table 6: **Typical Quiescent Supply Current**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
I_{CCINTQ}	Quiescent V_{CCINT} supply current	XC7K70T	241	241	241	187	mA
		XC7K160T	474	474	474	368	mA
		XC7K325T	810	810	810	629	mA
		XC7K355T	993	993	993	771	mA
		XC7K410T	1080	1080	1080	838	mA
		XC7K420T	1313	1313	1313	1019	mA
		XC7K480T	1313	1313	1313	1019	mA
I_{CCOQ}	Quiescent V_{CCO} supply current	XC7K70T	1	1	1	1	mA
		XC7K160T	1	1	1	1	mA
		XC7K325T	1	1	1	1	mA
		XC7K355T	1	1	1	1	mA
		XC7K410T	1	1	1	1	mA
		XC7K420T	1	1	1	1	mA
		XC7K480T	1	1	1	1	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current	XC7K70T	21	21	21	21	mA
		XC7K160T	40	40	40	40	mA
		XC7K325T	68	68	68	68	mA
		XC7K355T	75	75	75	75	mA
		XC7K410T	85	85	85	85	mA
		XC7K420T	99	99	99	99	mA
		XC7K480T	99	99	99	99	mA
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current	XC7K70T	N/A	N/A	N/A	N/A	mA
		XC7K160T	2	2	2	2	mA
		XC7K325T	2	2	2	2	mA
		XC7K355T	N/A	N/A	N/A	N/A	mA
		XC7K410T	2	2	2	2	mA
		XC7K420T	N/A	N/A	N/A	N/A	mA
		XC7K480T	N/A	N/A	N/A	N/A	mA

Table 6: **Typical Quiescent Supply Current *(Cont'd)***

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current	XC7K70T	6	6	6	6	mA
		XC7K160T	14	14	14	14	mA
		XC7K325T	19	19	19	19	mA
		XC7K355T	31	31	31	31	mA
		XC7K410T	34	34	34	34	mA
		XC7K420T	41	41	41	41	mA
		XC7K480T	41	41	41	41	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the XPower™ Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} have the same recommended voltage levels then they can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTX transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} - V_{MGTAVCC} > 150$ mV and $V_{MGTAVCC} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to 0.3 x $T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} - V_{CCINT} > 150$ mV and $V_{CCINT} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to 0.3 x T_{VCCINT} (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

Table 7 shows the minimum current, in addition to I_{CCQ}, that are required by Kintex-7 devices for proper power-on and configuration. If the current minimums shown in Table 6 and Table 7 are met, the device powers on after all five supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied.

Once initialized and configured, use the XPower tools to estimate current drain on these supplies.

Table 7: **Power-On Current for Kintex-7 Devices**

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	I_{CCAUX_IOMIN}	$I_{CCBRAMMIN}$	Units
	Typ(1)	Typ(1)	Typ(1)	Typ(1)	Typ(1)	
XC7K70T	I_{CCINTQ} + 450	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 40	mA
XC7K160T	I_{CCINTQ} + 550	I_{CCAUXQ} + 50	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 40	mA
XC7K325T	I_{CCINTQ} + 600	I_{CCAUXQ} + 80	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 40	mA
XC7K355T	I_{CCINTQ} + 1450	I_{CCAUXQ} + 109	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 81	mA
XC7K410T	I_{CCINTQ} + 1500	I_{CCAUXQ} + 125	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 90	mA
XC7K420T	I_{CCINTQ} + 2200	I_{CCAUXQ} + 180	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 108	mA
XC7K480T	I_{CCINTQ} + 2200	I_{CCAUXQ} + 180	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 108	mA

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. Use the XPower Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate maximum power-on currents.

Table 8: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
T_{VCCAUX_IO}	Ramp time from GND to 90% of V_{CCAUX_IO}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$	T_J = 100°C(1)	–	500	ms
		T_J = 85°C(1)	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 90% of $V_{MGTVCCAUX}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 9: **SelectIO DC Input and Output Levels** (1)(2)

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8	–8
HSTL_I_12	–0.300	V_{REF} – 0.080	V_{REF} + 0.080	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	6.3	–6.3
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8	–8
HSTL_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16	–16
HSTL_II_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16	–16
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 3	Note 3
LVCMOS15, LVDCI_15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	Note 4	Note 4
LVCMOS18, LVDCI_18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS25	–0.300	0.700	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 6	Note 6
LVCMOS33	–0.300	0.800	2.000	3.450	0.400	V_{CCO} – 0.400	Note 6	Note 6
LVTTL	–0.300	0.800	2.000	3.450	0.400	2.400	Note 7	Note 7
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	V_{CCO} + 0.300	10% V_{CCO}	90% V_{CCO}	0.1	–0.1
PCI33_3	–0.500	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.500	10% V_{CCO}	90% V_{CCO}	1.5	–0.5
SSTL12	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	14.25	–14.25
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.0	–13.0
SSTL135_R	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.9	–8.9
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.0	–13.0
SSTL15_R	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.9	–8.9
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8	–8
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.4	–13.4

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in 3.3V I/O banks.
3. Supported drive strengths of 2, 4, 6, or 8 mA in HP I/O banks and 4, 8, or 12 mA in HR I/O banks.
4. Supported drive strengths of 2, 4, 6, 8, 12, or 16 mA in HP I/O banks and 4, 8, 12, or 16 mA in HR I/O banks.
5. Supported drive strengths of 2, 4, 6, 8, 12, or 16 mA in HP I/O banks and 4, 8, 12, 16, or 24 mA in HR I/O banks.
6. Supported drive strengths of 4, 8, 12, or 16 mA
7. Supported drive strengths of 4, 8, 12, 16, or 24 mA
8. For detailed interface specific DC voltage levels, see UG471: *7 Series FPGAs SelectIO Resources User Guide*.

LVDS DC Specifications (LVDS_25)

The LVDS_25 standard is available in the HR I/O banks. See UG471: *7 Series FPGAs SelectIO Resources User Guide* for more information.

Table 12: **LVDS_25 DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.375	2.500	2.625	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.700	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input Common-Mode Voltage		0.300	1.200	1.425	V

LVDS DC Specifications (LVDS)

The LVDS standard is available in the HP I/O banks. See UG471: *7 Series FPGAs SelectIO Resources User Guide* for more information.

Table 13: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		1.710	1.800	1.890	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.825	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	Common-mode input voltage = 1.25V	100	350	600	mV
V_{ICM}	Input Common-Mode Voltage	Differential input voltage = ±350 mV	0.300	1.200	1.425	V

Table 18: **Maximum Physical Interface (PHY) Rate for Memory Interfaces (FBG Packages)(1)(2)**

Memory Standard	I/O Bank Type	V_{CCAUX_IO}(3)	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
4:1 Memory Controllers							
DDR3	HP	N/A	1333	1066	800	800	Mb/s
	HR	N/A	1066	800	800	800	Mb/s
DDR3L	HP	N/A	1066	800	667	667	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	N/A	800	800	800	800	Mb/s
	HR	N/A	800	667	667	667	Mb/s
RLDRAM III(4)	HP	N/A	550	500	450	450	MHz
	HR	N/A	N/A				
2:1 Memory Controllers							
DDR3	HP	N/A	1066	1066	800	800	Mb/s
	HR	N/A	1066	800	800	800	Mb/s
DDR3L	HP	N/A	1066	800	667	667	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	N/A	800	800	800	800	Mb/s
	HR	N/A	800	667	667	667	Mb/s
QDR II+(5)	HP	N/A	550	500	450	450	MHz
	HR	N/A	450	400	350	350	MHz
RLDRAM II	HP	N/A	533	500	450	450	MHz
	HR	N/A					
LPDDR2(4)	HP	N/A	667	667	667	667	Mb/s
	HR	N/A	667	667	533	533	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see UG586, *7 Series FPGAs Memory Interface Solutions User Guide*.
2. When using the internal V_{REF}, the maximum data rate is 800 Mb/s (400 MHz).
3. FBG packages do not have separate V_{CCAUX_IO} supply pins to adjust the pre-driver voltage of the HP I/O banks.
4. RLDRAM III (BL = 4, BL = 8) and LPDDR2 specifications have not been validated with memory IP.
5. The maximum QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations. Burst length 2 (BL = 2) implementations are limited to 333 MHz for all speed grades and I/O bank types.

Table 19: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVCMOS15_S16	0.66	0.69	0.81	0.90	1.76	1.95	2.13	1.91	2.52	2.81	3.12	2.42	ns
LVCMOS15_F4	0.66	0.69	0.81	0.90	3.39	3.60	3.80	1.98	4.15	4.46	4.79	2.50	ns
LVCMOS15_F8	0.66	0.69	0.81	0.90	1.79	1.99	2.18	1.92	2.55	2.85	3.17	2.44	ns
LVCMOS15_F12	0.66	0.69	0.81	0.90	1.40	1.54	1.65	1.67	2.16	2.40	2.64	2.19	ns
LVCMOS15_F16	0.66	0.69	0.81	0.90	1.37	1.51	1.61	1.66	2.13	2.37	2.60	2.17	ns
LVCMOS12_S4	0.88	0.91	1.00	1.01	3.85	4.22	4.69	2.89	4.61	5.08	5.68	3.41	ns
LVCMOS12_S8	0.88	0.91	1.00	1.01	2.52	2.96	3.52	2.41	3.28	3.82	4.51	2.92	ns
LVCMOS12_S12(1)	0.88	0.91	1.00	1.01	2.06	2.31	2.59	2.11	2.82	3.17	3.58	2.63	ns
LVCMOS12_F4	0.88	0.91	1.00	1.01	3.44	3.73	4.06	2.30	4.20	4.59	5.05	2.81	ns
LVCMOS12_F8	0.88	0.91	1.00	1.01	1.72	2.04	2.40	1.86	2.48	2.90	3.39	2.38	ns
LVCMOS12_F12(1)	0.88	0.91	1.00	1.01	1.54	1.71	1.87	1.69	2.30	2.57	2.86	2.20	ns
SSTL135_S	0.61	0.64	0.73	0.79	1.27	1.40	1.50	1.64	2.03	2.26	2.49	2.16	ns
SSTL15_S	0.61	0.64	0.73	0.73	1.24	1.37	1.47	1.59	2.00	2.23	2.46	2.11	ns
SSTL18_I_S	0.64	0.67	0.76	0.79	1.59	1.74	1.85	1.95	2.35	2.60	2.84	2.47	ns
SSTL18_II_S	0.64	0.67	0.76	0.78	1.27	1.40	1.50	1.63	2.03	2.26	2.49	2.14	ns
DIFF_SSTL135_S	0.59	0.61	0.73	0.79	1.27	1.40	1.50	1.64	2.03	2.26	2.49	2.16	ns
DIFF_SSTL15_S	0.63	0.67	0.77	0.79	1.24	1.37	1.47	1.59	2.00	2.23	2.46	2.11	ns
DIFF_SSTL18_I_S	0.65	0.69	0.78	0.79	1.50	1.63	1.72	1.95	2.26	2.49	2.71	2.47	ns
DIFF_SSTL18_II_S	0.65	0.69	0.78	0.79	1.13	1.22	1.25	1.66	1.89	2.08	2.24	2.17	ns
SSTL135_F	0.61	0.64	0.73	0.79	1.04	1.17	1.26	1.42	1.80	2.03	2.25	1.94	ns
SSTL15_F	0.61	0.64	0.73	0.73	1.04	1.17	1.26	1.39	1.80	2.03	2.25	1.91	ns
SSTL18_I_F	0.64	0.67	0.76	0.79	1.12	1.22	1.26	1.44	1.88	2.08	2.25	1.95	ns
SSTL18_II_F	0.64	0.67	0.76	0.78	1.05	1.18	1.28	1.42	1.81	2.04	2.27	1.94	ns
DIFF_SSTL135_F	0.59	0.61	0.73	0.79	1.04	1.17	1.26	1.42	1.80	2.03	2.25	1.94	ns
DIFF_SSTL15_F	0.63	0.67	0.77	0.79	1.04	1.17	1.26	1.39	1.80	2.03	2.25	1.91	ns
DIFF_SSTL18_I_F	0.65	0.69	0.78	0.79	1.10	1.19	1.23	1.52	1.86	2.05	2.22	2.03	ns
DIFF_SSTL18_II_F	0.65	0.69	0.78	0.79	1.02	1.10	1.14	1.50	1.78	1.96	2.13	2.02	ns

Notes:

1. This I/O standard is only available in the 3.3V high-range (HR) banks.

Table 21 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than T_{IOTPHZ} when the DCITERMDISABLE pin is used. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 21: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{IOTPHZ}	T input to pad high-impedance	0.76	0.86	0.99	0.62	ns
$T_{IOIBUFDISABLE\_HR}$	IBUF turn-on time from IBUFDISABLE to O output for HR I/O banks	1.72	1.89	2.14	2.17	ns
$T_{IOIBUFDISABLE\_HP}$	IBUF turn-on time from IBUFDISABLE to O output for HP I/O banks	1.31	1.46	1.76	1.86	ns

Table 23: **OLOGIC Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold						
T_{ODCK}/T_{OCKD}	D1/D2 pins Setup/Hold with respect to CLK	0.45/–0.13	0.50/–0.13	0.58/–0.13	0.79/–0.18	ns
T_{OOCECK}/T_{OCKOCE}	OCE pin Setup/Hold with respect to CLK	0.28/0.03	0.29/0.03	0.45/0.03	0.35/–0.10	ns
T_{OSRCK}/T_{OCKSR}	SR pin Setup/Hold with respect to CLK	0.32/0.18	0.38/0.18	0.70/0.18	0.62/–0.04	ns
T_{OTCK}/T_{OCKT}	T1/T2 pins Setup/Hold with respect to CLK	0.49/–0.16	0.56/–0.16	0.68/–0.16	0.67/–0.18	ns
T_{OTCECK}/T_{OCKTCE}	TCE pin Setup/Hold with respect to CLK	0.28/0.01	0.30/0.01	0.45/0.01	0.31/–0.10	ns
Combinatorial						
T_{ODQ}	D1 to OQ out or T1 to TQ out	0.73	0.81	0.97	1.18	ns
Sequential Delays						
T_{OCKQ}	CLK to OQ/TQ out	0.41	0.43	0.49	0.63	ns
$T_{RQ\_OLOGICE2}$	SR pin to OQ/TQ out (HP I/O banks only)	0.63	0.70	0.83	1.12	ns
$T_{GSRQ\_OLOGICE2}$	Global Set/Reset to Q outputs (HP I/O banks only)	7.60	7.60	10.51	11.39	ns
$T_{RQ\_OLOGICE3}$	SR pin to OQ/TQ out (HR I/O banks only)	0.63	0.70	0.83	1.12	ns
$T_{GSRQ\_OLOGICE3}$	Global Set/Reset to Q outputs (HR I/O banks only)	7.60	7.60	10.51	11.39	ns
Set/Reset						
$T_{RPW\_OLOGICE2}$	Minimum Pulse Width, SR inputs (HP I/O banks only)	0.54	0.54	0.63	0.68	ns, Min
$T_{RPW\_OLOGICE3}$	Minimum Pulse Width, SR inputs (HR I/O banks only)	0.54	0.54	0.63	0.68	ns, Min

Input Serializer/Deserializer Switching Characteristics

Table 24: **ISERDES Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold for Control Lines						
$T_{ISCCK\_BITSLIP}$/ $T_{ISCKC\_BITSLIP}$	BITSLIP pin Setup/Hold with respect to CLKDIV	0.01/0.12	0.02/0.13	0.02/0.15	0.02/0.21	ns
T_{ISCCK_CE}/ T_{ISCKC_CE}(2)	CE pin Setup/Hold with respect to CLK (for CE1)	0.39/–0.02	0.44/–0.02	0.63/–0.02	0.51/–0.22	ns
T_{ISCCK_CE2}/ T_{ISCKC_CE2}(2)	CE pin Setup/Hold with respect to CLKDIV (for CE2)	–0.12/0.29	–0.12/0.31	–0.12/0.35	–0.17/0.40	ns
Setup/Hold for Data Lines						
T_{ISDCK_D}/T_{ISCKD_D}	D pin Setup/Hold with respect to CLK	–0.02/0.11	–0.02/0.12	–0.02/0.15	–0.04/0.19	ns
T_{ISDCK_DDLY}/ T_{ISCKD_DDLY}	DDLY pin Setup/Hold with respect to CLK (using IDELAY)(1)	–0.02/0.11	–0.02/0.12	–0.02/0.15	–0.03/0.19	ns
$T_{ISDCK\_D\_DDR}$/ $T_{ISCKD\_D\_DDR}$	D pin Setup/Hold with respect to CLK at DDR mode	–0.02/0.11	–0.02/0.12	–0.02/0.15	–0.04/0.19	ns
$T_{ISDCK\_DDLY\_DDR}$/ $T_{ISCKD\_DDLY\_DDR}$	D pin Setup/Hold with respect to CLK at DDR mode (using IDELAY)(1)	0.11/0.11	0.12/0.12	0.15/0.15	0.19/0.19	ns
Sequential Delays						
T_{ISCKO_Q}	CLKDIV to out at Q pin	0.46	0.47	0.58	0.67	ns
Propagation Delays						
T_{ISDO_DO}	D input to DO output pin	0.09	0.10	0.12	0.14	ns

Notes:

1. Recorded at 0 tap value.
2. T_{ISCCK_CE2} and T_{ISCKC_CE2} are reported as T_{ISCCK_CE}/T_{ISCKC_CE} in TRACE report.

Input/Output Delay Switching Characteristics

Table 26: **Input/Output Delay Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
IDELAYCTRL						
T_{DLYCCO_RDY}	Reset to Ready for IDELAYCTRL	3.22	3.22	3.22	3.22	µs
$F_{IDELAYCTRL\_REF}$	Attribute REFCLK frequency = 200.00(1)	200.00	200.00	200.00	200.00	MHz
	Attribute REFCLK frequency = 300.00(1)	300.00	300.00	N/A	N/A	MHz
IDELAYCTRL_REF_PRECISION	REFCLK precision	±10	±10	±10	±10	MHz
$T_{IDELAYCTRL\_RPW}$	Minimum Reset pulse width	52.00	52.00	52.00	52.00	ns
IDELAY/ODELAY						
$T_{IDELAYRESOLUTION}$	IDELAY/ODELAY chain delay resolution	1/(32 x 2 x F_{REF})				ps
$T_{IDELAYPAT\_JIT}$ and $T_{ODELAYPAT\_JIT}$	Pattern dependent period jitter in delay chain for clock pattern.(2)	0	0	0	0	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23)(3)	±5	±5	±5	±5	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23)(4)	±9	±9	±9	±9	ps per tap
$T_{IDELAY\_CLK\_MAX}$/ $T_{ODELAY\_CLK\_MAX}$	Maximum frequency of CLK input to IDELAY/ODELAY	800.00	800.00	710.00	710.00	MHz
T_{IDCCK_CE} / T_{IDCKC_CE}	CE pin Setup/Hold with respect to C for IDELAY	0.11/0.10	0.14/0.12	0.18/0.14	0.14/0.16	ns
T_{ODCCK_CE} / T_{ODCKC_CE}	CE pin Setup/Hold with respect to C for ODELAY	0.14/0.03	0.16/0.04	0.19/0.05	0.28/0.06	ns
T_{IDCCK_INC}/ T_{IDCKC_INC}	INC pin Setup/Hold with respect to C for IDELAY	0.10/0.14	0.12/0.16	0.14/0.20	0.10/0.23	ns
T_{ODCCK_INC}/ T_{ODCKC_INC}	INC pin Setup/Hold with respect to C for ODELAY	0.10/0.07	0.12/0.08	0.13/0.09	0.19/0.16	ns
T_{IDCCK_RST}/ T_{IDCKC_RST}	RST pin Setup/Hold with respect to C for IDELAY	0.13/0.08	0.14/0.10	0.16/0.12	0.22/0.19	ns
T_{ODCCK_RST}/ T_{ODCKC_RST}	RST pin Setup/Hold with respect to C for ODELAY	0.16/0.04	0.19/0.06	0.24/0.08	0.32/0.11	ns
$T_{IDDO\_IDATAIN}$	Propagation delay through IDELAY	Note 5	Note 5	Note 5	Note 5	ps
$T_{ODDO\_ODATAIN}$	Propagation delay through ODELAY	Note 5	Note 5	Note 5	Note 5	ps

Notes:

1. Average Tap Delay at 200 MHz = 78 ps, at 300 MHz = 52 ps.
2. When HIGH_PERFORMANCE mode is set to TRUE or FALSE.
3. When HIGH_PERFORMANCE mode is set to TRUE.
4. When HIGH_PERFORMANCE mode is set to FALSE.
5. Delay depends on IDELAY/ODELAY tap setting. See TRACE report for actual values.

Table 32: **DSP48E1 Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup and Hold Times of the RST Pins						
$T_{DSPDCK\_\{RSTA; RSTB\}\_\{AREG; BREG\}}$/ $T_{DSPCKD\_\{RSTA; RSTB\}\_\{AREG; BREG\}}$	{RSTA, RSTB} input to {A, B} register CLK	0.34/ 0.10	0.39/ 0.11	0.47/ 0.13	0.53/ 0.34	ns
$T_{DSPDCK\_RSTC\_CREG}$/ $T_{DSPCKD\_RSTC\_CREG}$	RSTC input to C register CLK	0.06/ 0.22	0.07/ 0.24	0.08/ 0.26	0.08/ 0.31	ns
$T_{DSPDCK\_RSTD\_DREG}$/ $T_{DSPCKD\_RSTD\_DREG}$	RSTD input to D register CLK	0.37/ 0.06	0.42/ 0.06	0.50/ 0.07	0.57/ 0.07	ns
$T_{DSPDCK\_RSTM\_MREG}$/ $T_{DSPCKD\_RSTM\_MREG}$	RSTM input to M register CLK	0.18/ 0.18	0.20/ 0.21	0.23/ 0.24	0.24/ 0.29	ns
$T_{DSPDCK\_RSTP\_PREG}$/ $T_{DSPCKD\_RSTP\_PREG}$	RSTP input to P register CLK	0.24/ 0.01	0.26/ 0.01	0.30/ 0.01	0.37/ 0.00	ns
Combinatorial Delays from Input Pins to Output Pins						
$T_{DSPDO\_A\_CARRYOUT\_MULT}$	A input to CARRYOUT output using multiplier	3.21	3.69	4.39	5.60	ns
$T_{DSPDO\_D\_P\_MULT}$	D input to P output using multiplier	3.15	3.61	4.30	5.44	ns
$T_{DSPDO\_A\_P}$	A input to P output not using multiplier	1.30	1.48	1.76	2.10	ns
$T_{DSPDO\_C\_P}$	C input to P output	1.13	1.30	1.55	1.84	ns
Combinatorial Delays from Input Pins to Cascading Output Pins						
$T_{DSPDO\_\{A; B\}\_\{ACOUT; BCOUT\}}$	{A, B} input to {ACOUT, BCOUT} output	0.47	0.53	0.63	0.75	ns
$T_{DSPDO\_\{A, B\}\_CARRYCASCOUT\_MULT}$	{A, B} input to CARRYCASCOUT output using multiplier	3.44	3.94	4.69	5.96	ns
$T_{DSPDO\_D\_CARRYCASCOUT\_MULT}$	D input to CARRYCASCOUT output using multiplier	3.36	3.85	4.58	5.77	ns
$T_{DSPDO\_\{A, B\}\_CARRYCASCOUT}$	{A, B} input to CARRYCASCOUT output not using multiplier	1.50	1.72	2.04	2.44	ns
$T_{DSPDO\_C\_CARRYCASCOUT}$	C input to CARRYCASCOUT output	1.34	1.53	1.83	2.18	ns
Combinatorial Delays from Cascading Input Pins to All Output Pins						
$T_{DSPDO\_ACIN\_P\_MULT}$	ACIN input to P output using multiplier	3.09	3.55	4.24	5.42	ns
$T_{DSPDO\_ACIN\_P}$	ACIN input to P output not using multiplier	1.16	1.33	1.59	2.07	ns
$T_{DSPDO\_ACIN\_ACOUT}$	ACIN input to ACOUT output	0.32	0.37	0.45	0.53	ns
$T_{DSPDO\_ACIN\_CARRYCASCOUT\_MULT}$	ACIN input to CARRYCASCOUT output using multiplier	3.30	3.79	4.52	5.76	ns
$T_{DSPDO\_ACIN\_CARRYCASCOUT}$	ACIN input to CARRYCASCOUT output not using multiplier	1.37	1.57	1.87	2.40	ns
$T_{DSPDO\_PCIN\_P}$	PCIN input to P output	0.94	1.08	1.29	1.54	ns
$T_{DSPDO\_PCIN\_CARRYCASCOUT}$	PCIN input to CARRYCASCOUT output	1.15	1.32	1.57	1.88	ns
Clock to Outs from Output Register Clock to Output Pins						
$T_{DSPCKO\_P\_PREG}$	CLK PREG to P output	0.33	0.35	0.39	0.45	ns
$T_{DSPCKO\_CARRYCASCOUT\_PREG}$	CLK PREG to CARRYCASCOUT output	0.44	0.50	0.59	0.71	ns

Table 42: **Clock-Capable Clock Input to Output Delay With MMCM**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* MMCM.							
$T_{ICKOFMMCMCC}$	Clock-capable clock input and OUTFF *with* MMCM	XC7K70T	0.95	0.95	0.95	1.74	ns
		XC7K160T	0.96	0.96	0.96	1.78	ns
		XC7K325T	1.00	1.00	1.00	1.82	ns
		XC7K355T	1.00	1.00	1.00	1.78	ns
		XC7K410T	1.00	1.00	1.00	1.82	ns
		XC7K420T	1.07	1.07	1.07	1.82	ns
		XC7K480T	1.07	1.07	1.07	1.82	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

Table 43: **Clock-Capable Clock Input to Output Delay With PLL**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* PLL.							
$T_{ICKOFPLLCC}$	Clock-capable clock input and OUTFF *with* PLL	XC7K70T	0.84	0.84	0.84	1.45	ns
		XC7K160T	0.89	0.89	0.89	1.54	ns
		XC7K325T	0.89	0.89	0.89	1.54	ns
		XC7K355T	0.89	0.89	0.89	1.50	ns
		XC7K410T	0.89	0.89	0.89	1.54	ns
		XC7K420T	0.96	0.96	0.96	1.54	ns
		XC7K480T	0.96	0.96	0.96	1.54	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. PLL output jitter is already included in the timing calculation.

Table 44: **Pin-to-Pin, Clock-to-Out using BUFIO**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* BUFIO.						
$T_{ICKOFCS}$	Clock-to-Out of I/O clock for HR I/O banks	4.93	5.52	6.20	6.97	ns
	Clock-to-Out of I/O clock for HP I/O banks	4.85	5.44	6.11	6.90	ns

Table 53: **GTX Transceiver Performance *(Cont'd)***

Symbol	Description	Output Divider	Speed Grade								Units
			1.0V						0.9V		
			-3		-2/-2L		-1[1]		-2L[2]		
			Package Type								
			FF	FB	FF	FB	FF	FB	FF	FB	
$F_{GQPLLRANGE2}$	GTX transceiver QPLL frequency range 2		9.8–12.5		9.8–10.3125		N/A		N/A		GHz

Notes:

1. The -1 speed grade requires a 4-byte internal data width for operation above 5.0 Gb/s.
2. The -2L (0.9V) speed grade requires a 4-byte internal data width for operation above 3.8 Gb/s.
3. Data rates between 8.0 Gb/s and 9.8 Gb/s are not available.
4. For QPLL line rate range 2, the maximum line rate with the divider N set to 66 is 10.3125Gb/s.

Table 54: **GTX Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$F_{GTXDRPCLK}$	GTXDRPCLK maximum frequency	175.01	175.01	156.25	125.00	MHz

Table 55: **GTX Transceiver Reference Clock Switching Characteristics**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range	-3 speed grade	60	–	700	MHz
		All other speed grades	60	–	670	MHz
T_{RCLK}	Reference clock rise time	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle	Transceiver PLL only	40	50	60	%

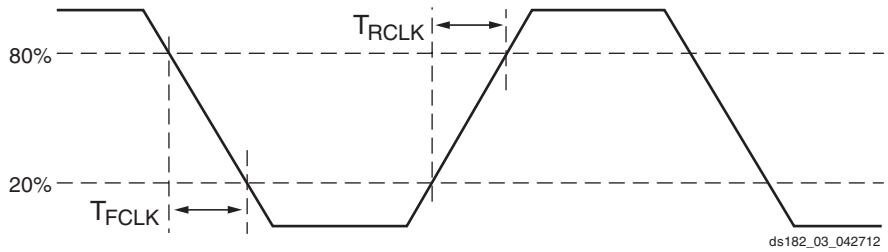

Figure 3: **Reference Clock Timing Parameters**

Table 56: **GTX Transceiver PLL /Lock Time Adaptation**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
T_{LOCK}	Initial PLL lock		–	–	1	ms
T_{DLOCK}	Clock recovery phase acquisition and adaptation time for decision feedback equalizer (DFE).	After the PLL is locked to the reference clock, this is the time it takes to lock the clock data recovery (CDR) to the data present at the input.	–	50,000	37 x10^6	UI
	Clock recovery phase acquisition and adaptation time for low-power mode (LPM) when the DFE is disabled.		–	50,000	2.3 x10^6	UI

Table 57: **GTX Transceiver User Clock Switching Characteristics(1)(2)**

Symbol	Description	Conditions	Speed Grade				Units
			1.0V			0.9V	
			-3(3)	-2/-2L(3)	-1(4)	-2L(5)	
F_{TXOUT}	TXOUTCLK maximum frequency		412.54	412.54	312.50	237.53	MHz
F_{RXOUT}	RXOUTCLK maximum frequency		412.54	412.54	312.50	237.53	MHz
F_{TXIN}	TXUSRCLK maximum frequency	16-bit data path	412.54	412.54	312.50	237.53	MHz
		32-bit data path	391.08	322.37	250.00	206.27	MHz
F_{RXIN}	RXUSRCLK maximum frequency	16-bit data path	412.54	412.54	312.50	237.53	MHz
		32-bit data path	391.08	322.37	250.00	206.27	MHz
F_{TXIN2}	TXUSRCLK2 maximum frequency	16-bit data path	412.54	412.54	312.50	237.53	MHz
		32-bit data path	391.08	322.37	250.00	206.27	MHz
		64-bit data path	195.54	161.19	125.00	103.14	MHz
F_{RXIN2}	RXUSRCLK2 maximum frequency	16-bit data path	412.54	412.54	312.50	237.53	MHz
		32-bit data path	391.08	322.37	250.00	206.27	MHz
		64-bit data path	195.54	161.19	125.00	103.14	MHz

Notes:

1. Clocking must be implemented as described in UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide*.
2. These frequencies are not supported for all possible transceiver configurations.
3. For speed grades -3, -2, -2L (1.0V), a 16-bit data path can only be used for speeds less than 6.6 Gb/s.
4. For speed grade -1, a 16-bit data path can only be used for speeds less than 5.0 Gb/s.
5. For speed grade -2L (0.9V), a 16-bit data path can only be used for speeds less than 3.8 Gb/s.

Table 58: **GTX Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTXTX}	Serial data rate range		0.500	–	F_{GTXMAX}	Gb/s
T_{RTX}	TX Rise time	20%–80%	–	40	–	ps
T_{FTX}	TX Fall time	80%–20%	–	40	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	500	ps
$V_{TXOOBVDPP}$	Electrical idle amplitude		–	–	15	mV
$T_{TXOOBTRANSITION}$	Electrical idle transition time		–	–	140	ns
$TJ_{12.5}$	Total Jitter(2)(4)	12.5 Gb/s	–	–	0.28	UI
$DJ_{12.5}$	Deterministic Jitter(2)(4)		–	–	0.17	UI
$TJ_{11.18}$	Total Jitter(2)(4)	11.18 Gb/s	–	–	0.28	UI
$DJ_{11.18}$	Deterministic Jitter(2)(4)		–	–	0.17	UI

Table 67: **XADC Specifications *(Cont'd)***

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
XADC Reference[5]						
External Reference	V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
On-Chip Reference		Ground V_{REFP} pin to AGND, T_j = –40°C to 100°C	1.2375	1.25	1.2625	V

Notes:

1. Offset and gain errors are removed by enabling the XADC automatic gain calibration feature. The values are specified for when this feature is enabled.
2. Only specified for new BitGen option XADCEnhancedLinearity = ON.
3. See the ADC chapter in UG480: *7 Series FPGAs XADC User Guide* for a detailed description.
4. See the Timing chapter in UG480: *7 Series FPGAs XADC User Guide* for a detailed description.
5. Any variation in the reference voltage from the nominal V_{REFP} = 1.25V and V_{REFN} = 0V will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by ±4% is permitted. On-chip reference variation is ±1%.

Configuration Switching Characteristics

Table 68: **Configuration Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Power-up Timing Characteristics						
T_{PL}[1]	Program latency	5	5	5	5	ms, Max
T_{POR}[1]	Power-on reset (50 ms ramp rate time)	10/50	10/50	10/50	10/50	ms, Min/Max
	Power-on reset (1 ms ramp rate time)	10/35	10/35	10/35	10/35	ms, Min/Max
$T_{PROGRAM}$	Program pulse width	250	250	250	250	ns, Min
CCLK Output (Master Mode)						
T_{ICCK}	Master CCLK output delay	150	150	150	150	ns, Min
T_{MCCKL}	Master CCLK clock Low time duty cycle	40/60	40/60	40/60	40/60	%, Min/Max
T_{MCCKH}	Master CCLK clock High time duty cycle	40/60	40/60	40/60	40/60	%, Min/Max
F_{MCCK}	Master CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
	Master CCLK frequency for AES encrypted x16	50.00	50.00	50.00	35.00	MHz, Max
F_{MCCK_START}	Master CCLK frequency at start of configuration	3.00	3.00	3.00	3.00	MHz, Typ
$F_{MCCKTOL}$	Frequency tolerance, master mode with respect to nominal CCLK	±50	±50	±50	±50	%, Max
CCLK Input (Slave Modes)						
T_{SCCKL}	Slave CCLK clock minimum Low time	2.50	2.50	2.50	2.50	ns, Min
T_{SCCKH}	Slave CCLK clock minimum High time	2.50	2.50	2.50	2.50	ns, Min
F_{SCCK}	Slave CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
EMCCLK Input (Master Mode)						
T_{EMCCKL}	External master CCLK Low time	2.50	2.50	2.50	2.50	ns, Min
T_{EMCCKH}	External master CCLK High time	2.50	2.50	2.50	2.50	ns, Min
F_{EMCCK}	External master CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
Internal Configuration Access Port						
F_{ICAPCK}	Internal configuration access port (ICAPE2)	100.00	100.00	100.00	70.00	MHz, Max

Table 68: **Configuration Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Master/Slave Serial Mode Programming Switching						
T_{DCCK}/T_{CCKD}	DIN Setup/Hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T_{CCO}	DOUT clock to out	8.00	8.00	8.00	9.00	ns, Max
SelectMAP Mode Programming Switching						
T_{SMDCCK}/T_{SMCCKD}	D[31:00] Setup/Hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
$T_{SMCSCCK}/T_{SMCCKCS}$	CSI_B Setup/Hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T_{SMWCCK}/T_{SMCCKW}	RDWR_B Setup/Hold	10.00/0.00	10.00/0.00	10.00/0.00	12.00/0.00	ns, Min
$T_{SMCKCSO}$	CSO_B clock to out (330 Ω pull-up resistor required)	7.00	7.00	7.00	8.00	ns, Max
T_{SMCO}	D[31:00] clock to out in readback	8.00	8.00	8.00	10.00	ns, Max
F_{RBCCK}	Readback frequency	100.00	100.00	100.00	70.00	MHz, Max
Boundary-Scan Port Timing Specifications						
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI Setup/Hold	3.00/2.00	3.00/2.00	3.00/2.00	3.00/2.00	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output	7.00	7.00	7.00	8.50	ns, Max
F_{TCK}	TCK frequency	66.00	66.00	66.00	50.00	MHz, Max
BPI Master Flash Mode Programming Switching						
T_{BPICCO}(2)	A[28:00], RS[1:0], FCS_B, FOE_B, FWE_B, ADV_B clock to out	8.50	8.50	8.50	10.00	ns, Max
T_{BPIDCC}/T_{BPICCD}	D[15:00] Setup/Hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
SPI Master Flash Mode Programming Switching						
T_{SPIDCC}/T_{SPICCD}	D[03:00] Setup/Hold	3.00/0.00	3.00/0.00	3.00/0.00	3.00/0.00	ns, Min
T_{SPICCM}	MOSI clock to out	8.00	8.00	8.00	9.00	ns, Max
$T_{SPICCFC}$	FCS_B clock to out	8.00	8.00	8.00	9.00	ns, Max

Notes:

1. To support longer delays in configuration, use the design solutions described in UG470: *7 Series FPGA Configuration User Guide*.
2. Only during configuration, the last edge is determined by a weak pull-up/pull-down resistor in the I/O.

eFUSE Programming Conditions

Table 69 lists the programming conditions specifically for eFUSE. For more information, see UG470: *7 Series FPGA Configuration User Guide*.

Table 69: **eFUSE Programming Conditions(1)**

Symbol	Description	Min	Typ	Max	Units
I_{FS}	V_{CCAUX} supply current	–	–	115	mA
t_j	Temperature range	15	–	125	°C

Notes:

1. The FPGA must not be configured during eFUSE programming.